查询"BT138F"供应商

BT138F series

GENERAL DESCRIPTION

Glass passivated triacs in a full pack plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

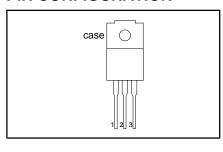
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BT138F- BT138F- BT138F-	500 500F 500G	600 600F 600G	800 800F 800G	
V_{DRM}	Repetitive peak off-state	500	600	800	V
I _{T(RMS)} I _{TSM}	voltages RMS on-state current Non-repetitive peak on-state current	12 90	12 90	12 90	A A

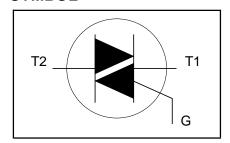
PINNING - SOT186

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-500 500 ¹	-600 600 ¹	-800 800	\ \
$I_{T(RMS)}\\I_{TSM}$	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{hs} \le 56 ^{\circ}\text{C}$ full sine wave; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{DRM(max)}$	-		12		А
		t = 20 ms t = 16.7 ms	-		90 100		Α
l ² t dl _T /dt	I ² t for fusing Repetitive rate of rise of on-state current after	t = 10.7 ms t = 10 ms $I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-		40		A A ² s
	triggering	T2+ G+ T2+ G- T2- G- T2- G+	- - -		50 50 50		A/μs A/μs A/μs
I _{GM} V _{GM} P _{GM}	Peak gate current Peak gate voltage Peak gate power	12- 9+	-		10 2 5 5		A/μs A V W
P _{G(AV)} T _{stg}	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- -40 -		0.5 150 125		ο̈́ο

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 $A/\mu s$.

Philips Semiconductors Product specification

BT138F series

ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. ≤ 65% ; clean and dustfree	-		1500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	12	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink Thermal resistance	full or half cycle with heatsink compound without heatsink compound in free air	-	- - 55	4.0 5.5	K/W K/W K/W
I ¹ ` th i-a	junction to ambient	III liee all		55		rv, v v

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.			UNIT
I _{GT}	Gate trigger current	BT138F - $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				F	G	
'GI	Gate trigger ourrent	T2+ G+ T2+ G-	-	5 8	35 35	25 25	50 50	mA mA
		T2- G- T2- G- T2- G+	-	10 22	35 70	25 70	50 50 100	mA mA
IL	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	_	7				
		T2+ G+ T2+ G- T2- G-	-	20 8	40 60	40 60	60 90	mA mA
	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	10 6	40 60 30	40 60 30	60 90 60	mA mA mA
l I _H] "	_		30		00	
V_{T}	On-state voltage Gate trigger voltage	$I_T = 15 \text{ A}$ $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$ $V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$	- - 0.25	1.4 0.7 0.4		1.65 1.5 -		V V V
I _D	Off-state leakage current	$T_{j} = 125 ^{\circ}\text{C}$ $V_{D} = V_{DRM(max)};$ $T_{j} = 125 ^{\circ}\text{C}$	-	0.1		0.5		mA

BT138F series

DYNAMIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		TYP.	MAX.	UNIT
dV _D /dt	Critical rate of change of off-state voltage	BT138F - $V_{DM} = 67\% V_{DRM(max)};$ $T_i = 125 °C;$ exponential	 100	F 50	G 200	250	-	V/μs
dV _{com} /dt	Critical rate of change of	waveform; gate open circuit $V_{DM} = 400 \text{ V}; T_j = 95 ^{\circ}\text{C};$ $I_{T(RMS)} = 12 \text{ A};$ $dI_{com}/dt = 5.4 \text{ A/ms}; gate$	-	-	10	20	-	V/μs
t _{gt}	Gate controlled turn-on time	open circuit $I_{TM} = 16 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu s$	ı	-	ı	2	1	μs

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BT138F series

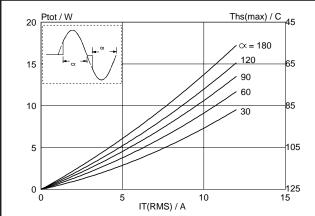


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha =$ conduction angle.

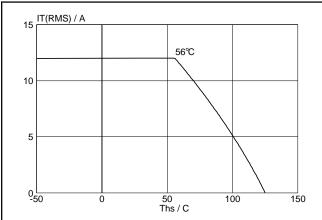


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs} .

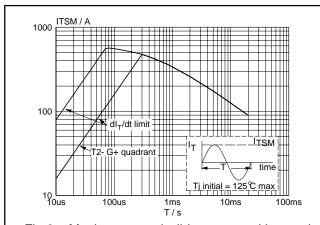


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

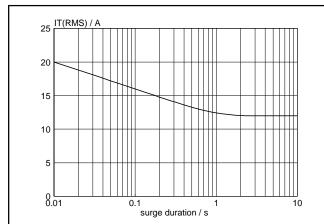


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \le 56$ °C.

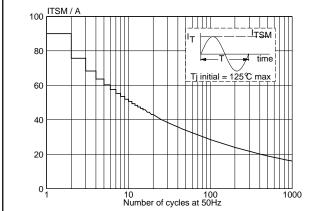


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

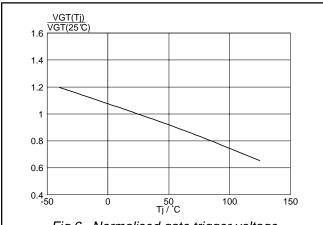
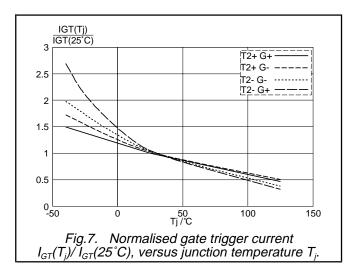
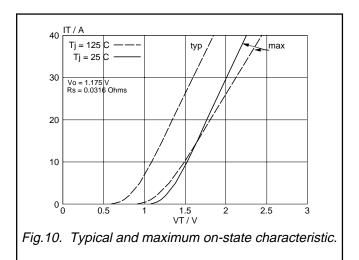


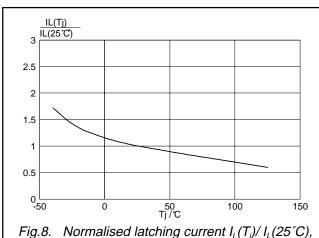
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25\,^{\circ}C)$, versus junction temperature T_j .

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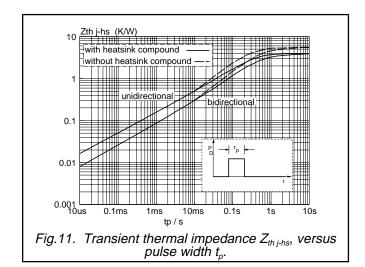
BT138F series

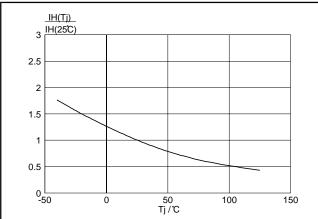






versus junction temperature T





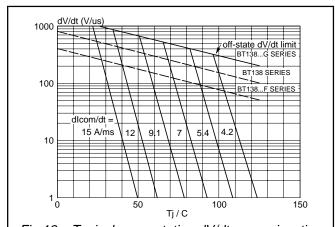


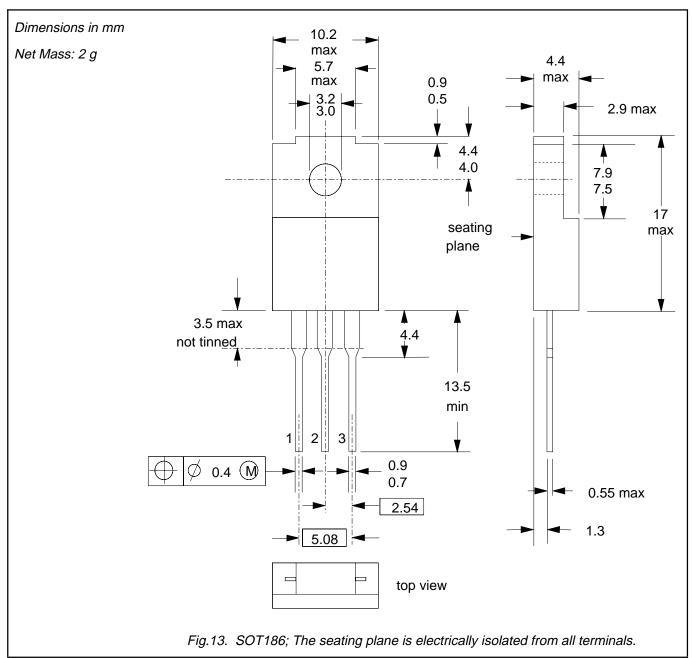
Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$, versus junction temperature T_i .

Fig.12. Typical commutation dV/dt versus junction temperature, parameter commutation d $_{7}$ /dt. The triac should commutate when the dV/dt is below the value on the appropriate curve for pre-commutation d $_{7}$ /dt.

電源"BT138F"供应商

BT138F series

MECHANICAL DATA



- Accessories supplied on request: refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

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BT138F series

DEFINITIONS

Data sheet status							
Objective specification	This data sheet contains target or goal specifications for product development.						
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.						
Product specification	This data sheet contains final product specifications.						

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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